2.0x1.25mm PHOTOTRANSISTOR

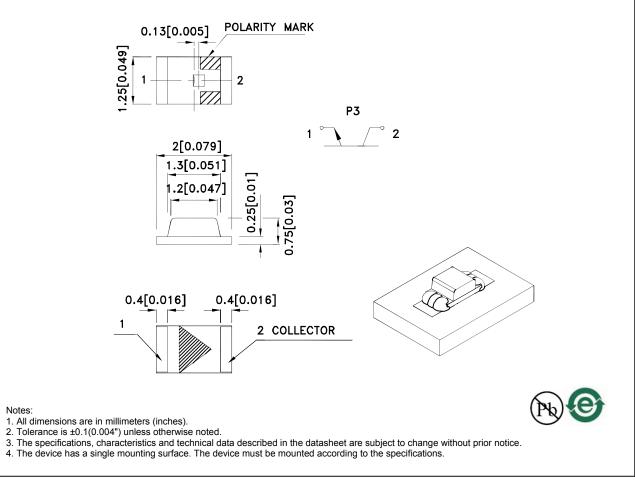
Part Number: APT2012P3BT

Features

- 2.0mmx1.25mm SMT LED,0.75mm thickness.
- Mechanically and spectrally matched to infrared emitting LED lamp.
- Package: 2000pcs / reel .
- Blue transparent lens.
- Moisture sensitivity level : level 3.
- RoHS compliant.

Description Made with NPN silicon phototransistor chips.

Package Dimensions



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Electrical / Optical Characteristics at TA=25°C

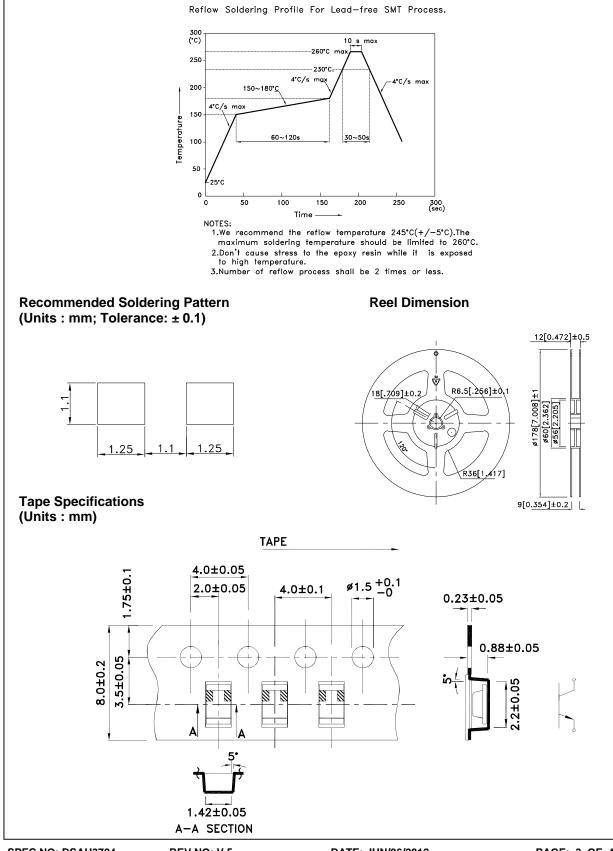
Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
VBR CEO	Collector-to-Emitter Breakdown Voltage	30			v	lc=100uA Ee=0mW/c
VBR ECO	Emitter-to-Collector Breakdown Voltage	5			v	l∈=100uA Ee=0mW/c mঁ
VCE (SAT)	Collector-to-Emitter Saturation Voltage			0.8	v	lc=2mA Ee=20mW/c mঁ
I ceo	Collector Dark Current			100	nA	Vce=10V Ee=0mW/c mឺ
Tr	Rise Time (10% to 90%)		15		us	Vce = 5V Ic=1mA RL=1000Ω
TF	Fall Time (90% to 10%)		15		us	
I (ON)	On State Collector Current	0.1	0.3		mA	VcE = 5V Ee=1mW/c mឺ λ=940nm
201/2	Angle of half sensitivity		120		deg	

Absolute Maximum Ratings at TA=25°C

Parameter	Max.Ratings		
Collector-to-Emitter Voltage	30V		
Emitter-to-Collector Voltage	5V		
Power Dissipation at (or below) 25°C Free Air Temperature	100mW		
Operating Temperature	-40°C To +85°C		
Storage Temperature	-40°C To +85°C		

APT2012P3BT

Reflow soldering is recommended and the soldering profile is shown below. Other soldering methods are not recommended as they might cause damage to the product.



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